

## Ordering Information

Part Number	Qty / Reel	Description
TFDU4100-TR3	1000 pcs	Oriented in carrier tape for side view surface mounting
TFDU4100-TT3	1000 pcs	Oriented in carrier tape for top view surface mounting
TFDS4500-TR3	750 pcs	
TFDT4500-TR3	750 pcs	

## Functional Block Diagram

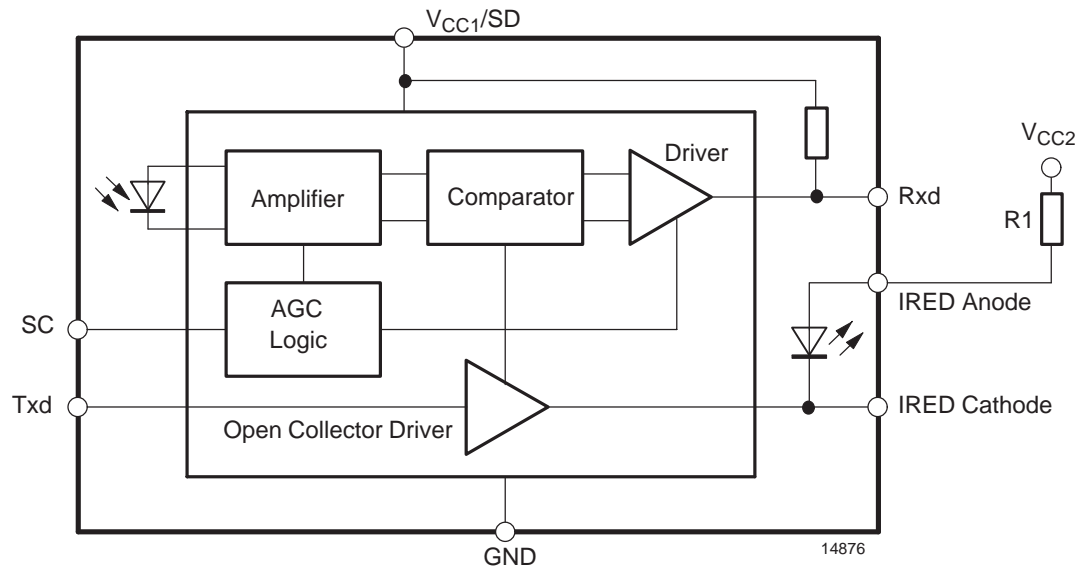
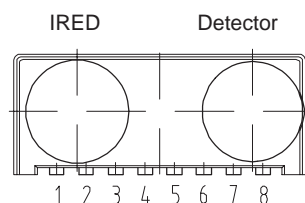


Figure 1. Functional Block Diagram

## Pin Description

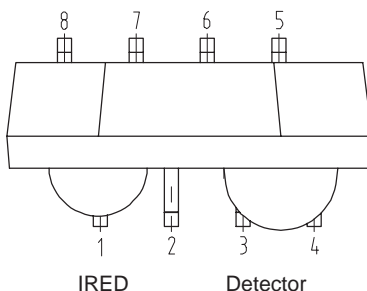
Pin Number		Function	Description	I/O	Active
"U" and "T" Option	"S" Option				
1	8	IRED Anode	IRED anode, should be externally connected to $V_{CC2}$ through a current control resistor		
2	1	IRED Cathode	IRED cathode, internally connected to driver transistor		
3	7	Txd	Transmit Data Input	I	HIGH
4	2	Rxd	Received Data Output, open collector. No external pull-up or pull-down resistor is required (20 k $\Omega$ resistor internal to device). Pin is inactive during transmission.	O	LOW
5	6	NC	Do not connect		
6	3	$V_{CC1}$ / SD	Supply Voltage / Shutdown		
7	5	SC	Sensitivity control	I	HIGH
8	4	GND	Ground		

“U” Option BabyFace (Universal)



14885

“S” Option Side View



“T” Option Top View

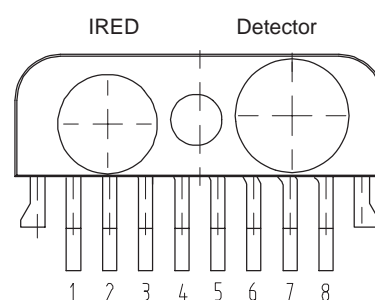


Figure 2. Pinings

## Absolute Maximum Ratings

Reference point Pin GND unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Supply Voltage Range	$0\text{ V} \leq V_{CC2} \leq 6\text{ V}$	$V_{CC1}$	-0.5		6	V
	$0\text{ V} \leq V_{CC1} \leq 6\text{ V}$	$V_{CC2}$	-0.5		6	V
Input Currents	For all Pins, except IRED Anode Pin				10	mA
Output Sink Current					25	mA
Power Dissipation	See Derating Curve	$P_D$			200	mW
Junction Temperature		$T_J$			125	°C
Ambient Temperature Range (Operating)		$T_{amb}$	-25		+85	°C
Storage Temperature Range		$T_{stg}$	-25		+85	°C
Soldering Temperature	See Recommended Solder Profile			215	240	°C
Average IRED Current		$I_{IRED} (DC)$			100	mA
Repetitive Pulsed IRED Current	$t < 90\text{ }\mu\text{s}$ , $t_{on} < 20\%$	$I_{IRED} (RP)$			500	mA
IRED Anode Voltage		$V_{IRED A}$	-0.5		6	V
Transmitter Data Input Voltage		$V_{Txd}$	-0.5		$V_{CC1}+0.5$	V
Receiver Data Output Voltage		$V_{Rxd}$	-0.5		$V_{CC1}+0.5$	V
Virtual Source Size	Method: (1-1/e) encircled energy	d	2.5	2.8		mm
Maximum Intensity for Class 1 Operation of IEC825-1 or EN60825-1 (worst case IrDA SIR pulse pattern *)	EN60825, 1997				400	mW/sr

\* Note:

Transmitted data: continuously transmitted “0”. In normal data transfer operation “0” and “1” will be transmitted with the same probability. Therefore, for that case, about a factor of two of safety margin is included. However, for worst case thermal stress testing such data pattern are often used and for this case the 400 mW/sr value has to be taken.

## Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ ,  $V_{CC} = 2.7\text{ V}$  to  $5.5\text{ V}$  unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

Parameters	Test Conditions / Pins	Symbol	Min.	Typ.	Max.	Unit
<b>Transceiver</b>						
Supply Voltage	Receive Mode Transmit Mode, $R_2 = 47\ \Omega$ (see Recommended Application Circuit)	$V_{CC1}$ $V_{CC2}$	2.7 2.0		5.5 5.5	V V
Supply Current Pin $V_{CC1}$ (Receive Mode)	$V_{CC1} = 5.5\text{ V}$ $V_{CC1} = 2.7\text{ V}$	$I_{CC1} (R_x)$		1.3 1.0	2.5 1.5	mA mA
Supply Current Pin $V_{CC1}$ (avg) (Transmit Mode)	$I_{RED} = 210\text{ mA}$ (at IRED Anode Pin) $V_{CC1} = 5.5\text{ V}$ $V_{CC1} = 2.7\text{ V}$	$I_{CC1} (T_x)$		5.0 3.5	5.5 4.5	mA mA
Leakage Current of IR Emitter, IRED Anode Pin	$V_{CC1} = \text{OFF}$ , $T_{XD} = \text{LOW}$ , $V_{CC2} = 6\text{ V}$ , $T = 25\text{ to }85^{\circ}\text{C}$	$I_L (IRED_A)$		0.005	0.5	$\mu\text{A}$
Transceiver Power On Settling Time		$T_{PON}$		50		$\mu\text{s}$

## Optoelectronic Characteristics

$T_{amb} = 25^{\circ}\text{C}$ ,  $V_{CC} = 2.7\text{ V}$  to  $5.5\text{ V}$  unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
<b>Receiver</b>						
Minimum Detection Threshold Irradiance	$\text{BER} = 10^{-8}$ (IrDA Specification) $\alpha = \pm 15^{\circ}$ , SIR Mode, SC = LOW	$E_e$		20	35	$\text{mW}/\text{m}^2$
	$\alpha = \pm 15^{\circ}$ , SIR Mode, SC = HIGH	$E_e$	6	10	15	$\text{mW}/\text{m}^2$
Maximum Detection Threshold Irradiance	$\alpha = \pm 90^{\circ}$ , SIR Mode, $V_{CC1} = 5\text{ V}$	$E_e$	3.3	5		$\text{kW}/\text{m}^2$
	$\alpha = \pm 90^{\circ}$ , SIR Mode, $V_{CC1} = 3\text{ V}$	$E_e$	8	15		$\text{kW}/\text{m}^2$
Logic LOW Receiver Input Irradiance	SC = HIGH or LOW	$E_e$			4	$\text{mW}/\text{m}^2$
Output Voltage – Rxd	Active, $C = 15\text{ pF}$ , $R = 2.2\text{ k}\Omega$	$V_{OL}$		0.5	0.8	V
	Non-active, $C = 15\text{ pF}$ , $R = 2.2\text{ k}\Omega$	$V_{OH}$	$V_{CC1} - 0.5$			V
Output Current – Rxd	$V_{OL} < 0.8\text{ V}$	$I_{OL}$		4		mA
Rise Time – Rxd	$C = 15\text{ pF}$ , $R = 2.2\text{ k}\Omega$	$t_r (R_{xd})$	20		1400	ns
Fall Time – Rxd	$C = 15\text{ pF}$ , $R = 2.2\text{ k}\Omega$	$t_f (R_{xd})$	20		200	ns
Pulse Width – Rxd Output	Input pulse width = $1.6\ \mu\text{s}$ , 115.2 kbit/s	$t_{PW}$	1.41		8	$\mu\text{s}$
Jitter, Leading Edge of Output Signal	Over a Period of 10 bit, 115.2 kbit/s	$t_j$			2	$\mu\text{s}$
Latency		$t_L$		100	500	$\mu\text{s}$



## Optoelectronic Characteristics

$T_{amb} = 25^{\circ}\text{C}$ ,  $V_{CC} = 2.7\text{ V}$  to  $5.5\text{ V}$  unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
<b>Transmitter</b>						
IRE Operating Current	IRE Operating Current can be adjusted by Variation of R1. Current Limiting Resistor is in Series to IRE: $R1 = 14\ \Omega$ , $V_{CC2} = 5.0\text{ V}$	$I_{IRE}$		0.2	0.28	A
Logic LOW Transmitter Input Voltage		$V_{IL} (Txd)$	0		0.8	V
Logic HIGH Transmitter Input Voltage		$V_{IH} (Txd)$	2.4		$V_{CC1}+0.5$	V
Output Radiant Intensity	In Agreement with IEC825 Eye Safety Limit, if Current Limiting Resistor is in Series to IRE: $R1 = 14\ \Omega$ , $V_{CC2} = 5.0\text{ V}$ , $\alpha = \pm 15^{\circ}$	$I_e$	45	140	200	mW/sr
	Txd Logic LOW Level	$I_e$			0.04	mW/sr
Angle of Half Intensity		$a$		$\pm 24$		$^{\circ}$
Peak Wavelength of Emission		$\lambda_P$	880		900	nm
Half-Width of Emission Spectrum				60		nm
Optical Rise Time, Fall Time		$t_{ropt}$ , $t_{fopt}$		200	600	ns
Optical Overshoot					25	%
Rising Edge Peak-to-Peak Jitter of Optical Output Pulse	Over a Period of 10 bits, Independent of Information content				0.2	$\mu\text{s}$

### Recommended Circuit Diagram

The only required components for designing an IrDA 1.2 compatible design using Telefunken SIR transceivers are a current limiting resistor to the IRED. However, depending on the entire system design and board layout, additional components may be required (see figure 3). It is recommended that the capacitors C1 and C2 are positioned as near as possible to the transceiver power supply pins. A tantalum capacitor should be used for C1, while a ceramic capacitor should be used for C2 to suppress RF noise. Also, when connecting the described circuit to the power supply, low impedance wiring should be used.

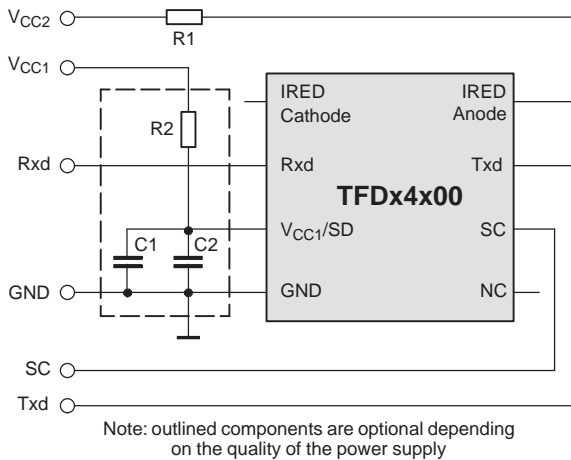


Figure 3. Recommended Application Circuit

R1 is used for controlling the current through the IR emitter. For increasing the output power of the IRED, the value of the resistor should be reduced. Similarly, to reduce the output power of the IRED, the value of the resistor should be increased. For typical values of R1 (see figures 4 and 5), e.g. for IrDA compliant operation ( $V_{CC2} = 5\text{ V} \pm 5\%$ ), a current control resistor of  $14\ \Omega$  is recommended. The upper drive current limitation is dependent on the duty cycle and is given by the absolute maximum ratings on the data sheet and the eye safety limitations given by IEC825-1. R2, C1 and C2 are optional and dependent on the quality of the supply voltage  $V_{CC1}$  and injected noise. An unstable power supply with dropping voltage during transmission may reduce sensitivity (and transmission range) of the transceiver.

Table 1. Recommended Application Circuit Components

Component	Recommended Value	Vishay Part Number
C1	4.7 $\mu\text{F}$ , Tantalum	293D 475X9 016B 2T
C2	0.1 $\mu\text{F}$ , Ceramic	VJ 1206 Y 104 J XXMT
R1	14 $\Omega$ , 0.25 W (recommended using two 7 $\Omega$ , 0.125 W resistors in series)	CRCW-1206-7R00-F-RT1
R2	47 $\Omega$ , 0.125 W	CRCW-1206-47R0-F-RT1

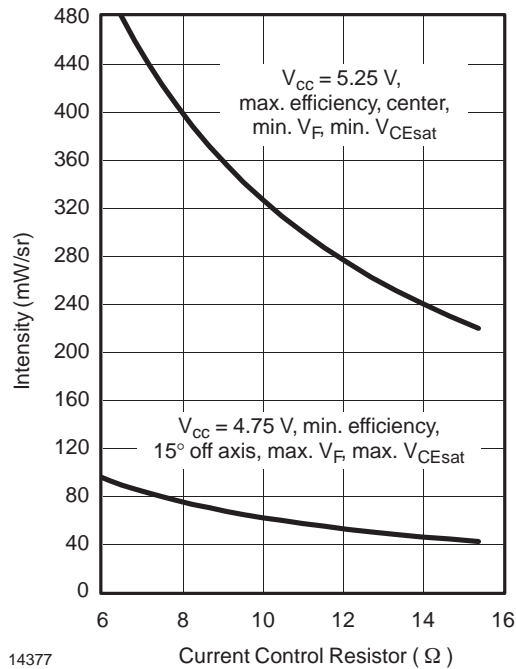


Figure 4.  $I_e$  vs. R1

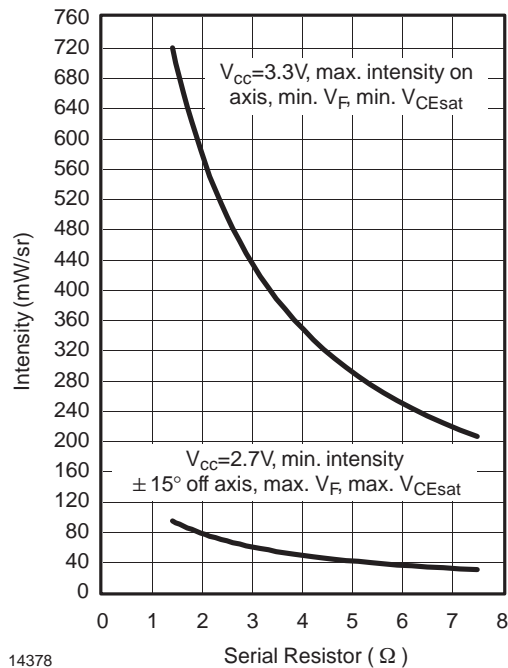


Figure 5.  $I_e$  vs. R1

The sensitivity control (SC) pin allows the minimum detection irradiance threshold of the transceiver to be lowered when set to a logic HIGH. Lowering the irradiance threshold increases the sensitivity to infrared signals and increases transmission range up to 3 meters. However, setting the Pin SC to logic HIGH also makes the transceiver more susceptible to transmission errors due to an increased sensitivity to fluorescent light disturbances. It is recommended to set the Pin SC to logic LOW or left open if the increased range is not required or if the system will be operating in bright ambient light.

The guide pins on the side-view and top-view packages are internally connected to ground but should not be connected to the system ground to avoid ground loops. They should be used for mechanical purposes only and should be left floating.

## Shutdown

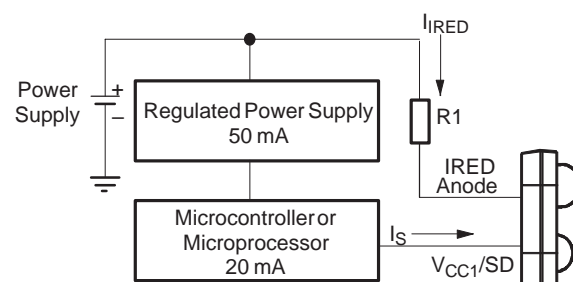
The internal switch for the IRED in Telefunken SIR transceivers is designed to be operated like an open collector driver. Thus, the  $V_{CC2}$  source can be an unregulated power supply while only a well regulated power source with a supply current of 1.3 mA connected to  $V_{CC1}/SD$  is needed to provide power to the remainder of the transceiver circuitry in receive mode. In transmit mode, this current is slightly higher (approximately 4 mA average at 3 V supply current) and the voltage is not required to be kept as stable as in receive mode. A voltage drop of  $V_{CC1}$  is acceptable down to about 2.0 V when buffering the voltage directly from the Pin  $V_{CC1}$  to GND see figure 3).

This configuration minimizes the influence of high current surges from the IRED on the internal analog control circuitry of the transceiver and the application circuit. Also board space and cost savings can be achieved by eliminating the additional linear regulator normally needed for the IRED's high current requirements.

The transceiver can be very efficiently shutdown by keeping the IRED connected to the power supply  $V_{CC2}$  but switching off  $V_{CC1}/SD$ . The power source to  $V_{CC1}/SD$  can be provided directly from a microcontroller (see figure 6). In shutdown, current loss is realized only as leakage current through the current limiting resistor to the IRED (typically 5 nA). The settling time after switching  $V_{CC1}/SD$  on again is

approximately 50  $\mu$ s. Telefunken's TOIM3232 interface circuit is designed for this shutdown feature. The  $V_{CC\_SD}$ , S0 or S1 outputs on the TOIM3232 can be used to power the transceiver with the necessary supply current.

If the microcontroller or the microprocessor is unable to drive the supply current required by the transceiver, a low-cost SOT23 pnp transistor can be used to switch voltage on and off from the regulated power supply (see figure 7). The additional component cost is minimal and saves the system designer additional power supply costs.



TFDU4100 (Note: Typical Values Listed)

Receive Mode

@ 5 V:  $I_{IRED} = 210$  mA,  $I_S = 1.3$  mA

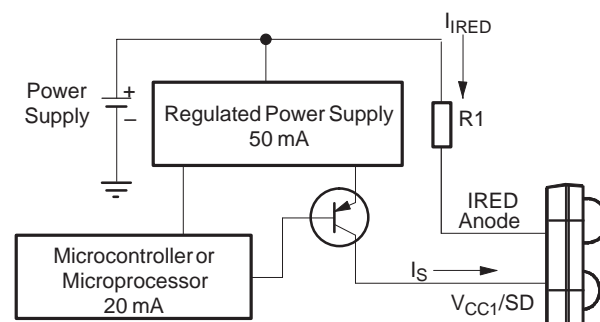
@ 2.7 V:  $I_{IRED} = 210$  mA,  $I_S = 1.0$  mA

Transmit Mode

@ 5 V:  $I_{IRED} = 210$  mA,  $I_S = 5$  mA (Avg.)

@ 2.7 V:  $I_{IRED} = 210$  mA,  $I_S = 3.5$  mA (Avg.) 14878

Figure 6.



TFDU4100 (Note: Typical Values Listed)

Receive Mode

@ 5 V:  $I_{IRED} = 210$  mA,  $I_S = 1.3$  mA

@ 2.7 V:  $I_{IRED} = 210$  mA,  $I_S = 1.0$  mA

Transmit Mode

@ 5 V:  $I_{IRED} = 210$  mA,  $I_S = 5$  mA (Avg.)

@ 2.7 V:  $I_{IRED} = 210$  mA,  $I_S = 3.5$  mA (Avg.) 14879

Figure 7.

## Recommended SMD Pad Layout

The leads of the device should be soldered in the center position of the pads.

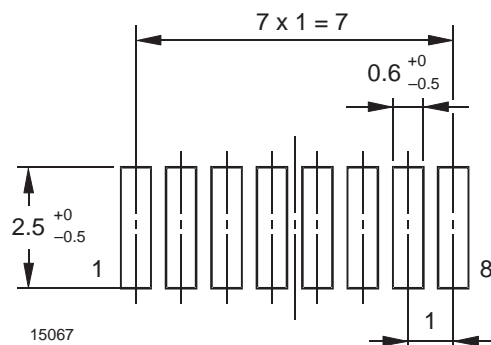


Figure 8. TFDU4100 BabyFace (Universal)

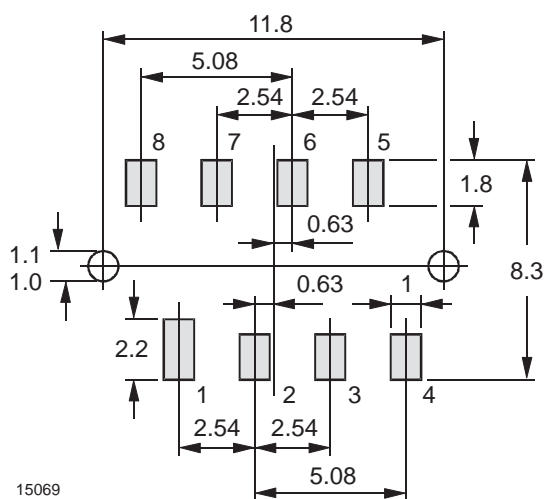


Figure 9. TFDS4500 Side View Package

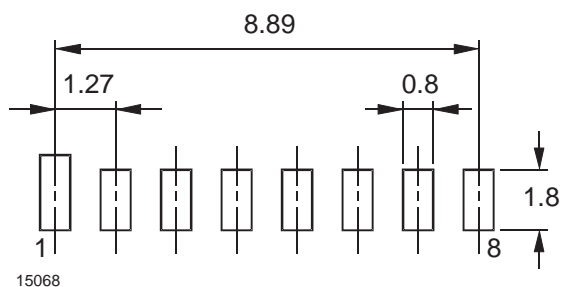


Figure 10. TFDT4500 Top View Package

Note: Leads of the device should be at least 0.3 mm within the ends of the pads.  
Pad 1 is longer to designate Pin 1 connection to transceiver.

## Recommended Solder Profile

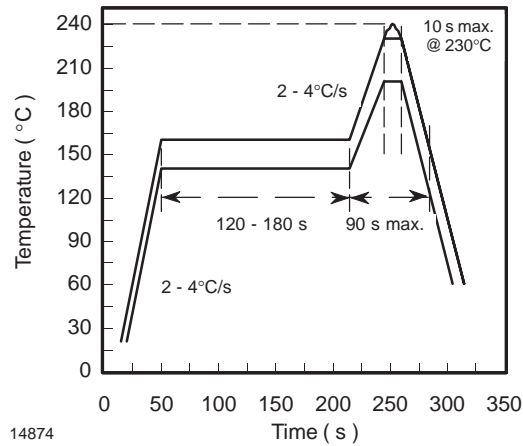


Figure 11. Recommended Solder Profile

## Current Derating Diagram

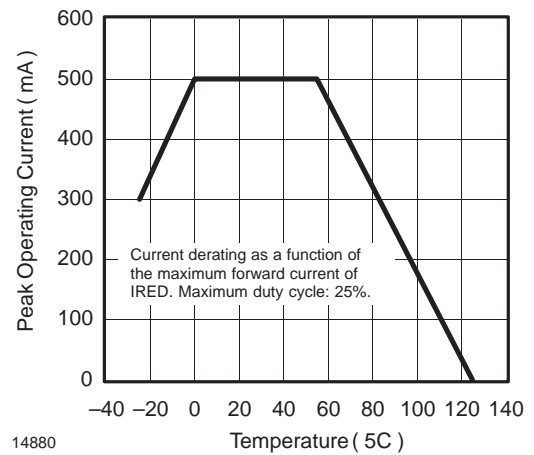
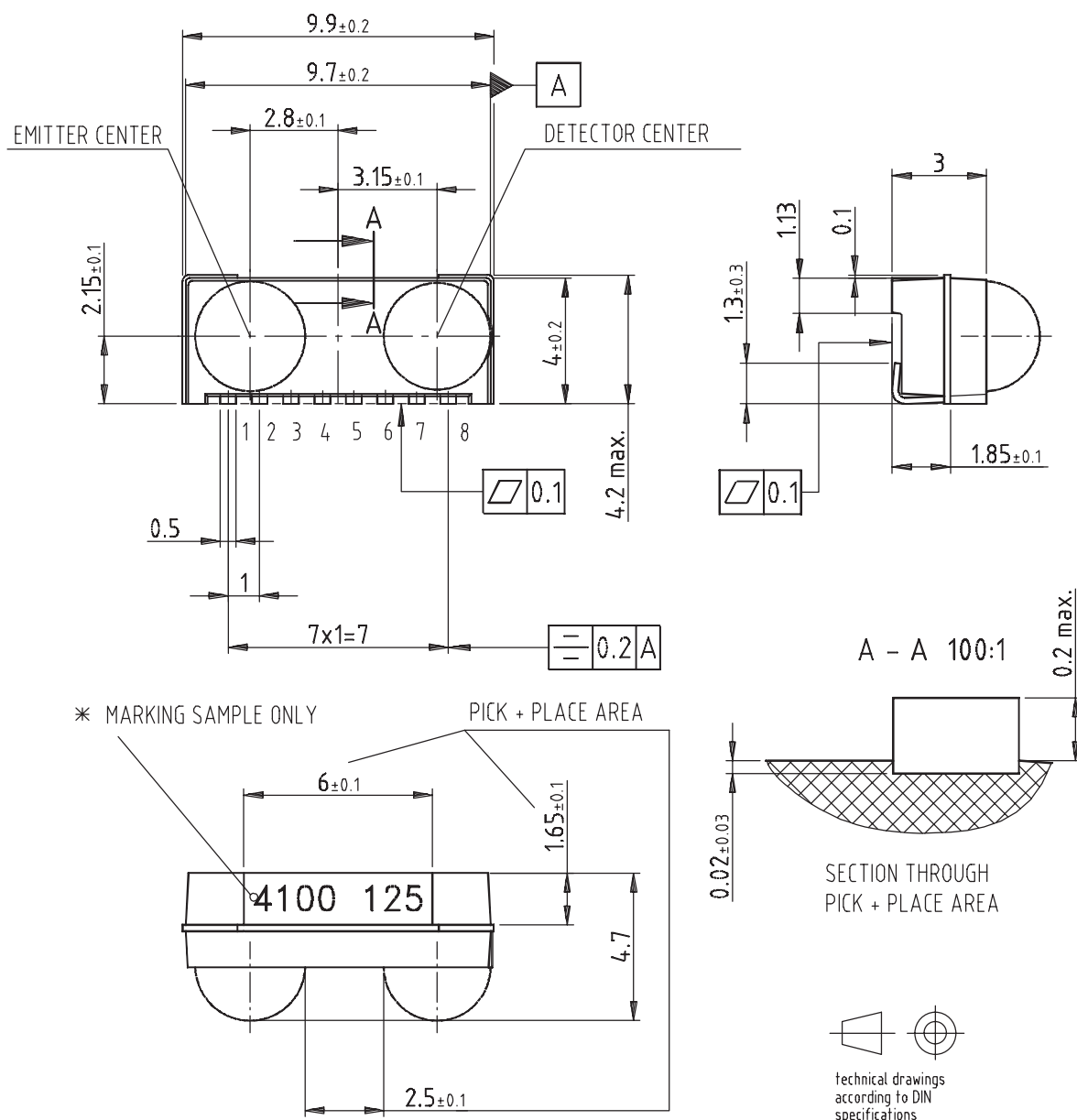


Figure 12. Current Derating Diagram



## TFDU4100 – BabyFace (Universal) Package (Mechanical Dimensions)

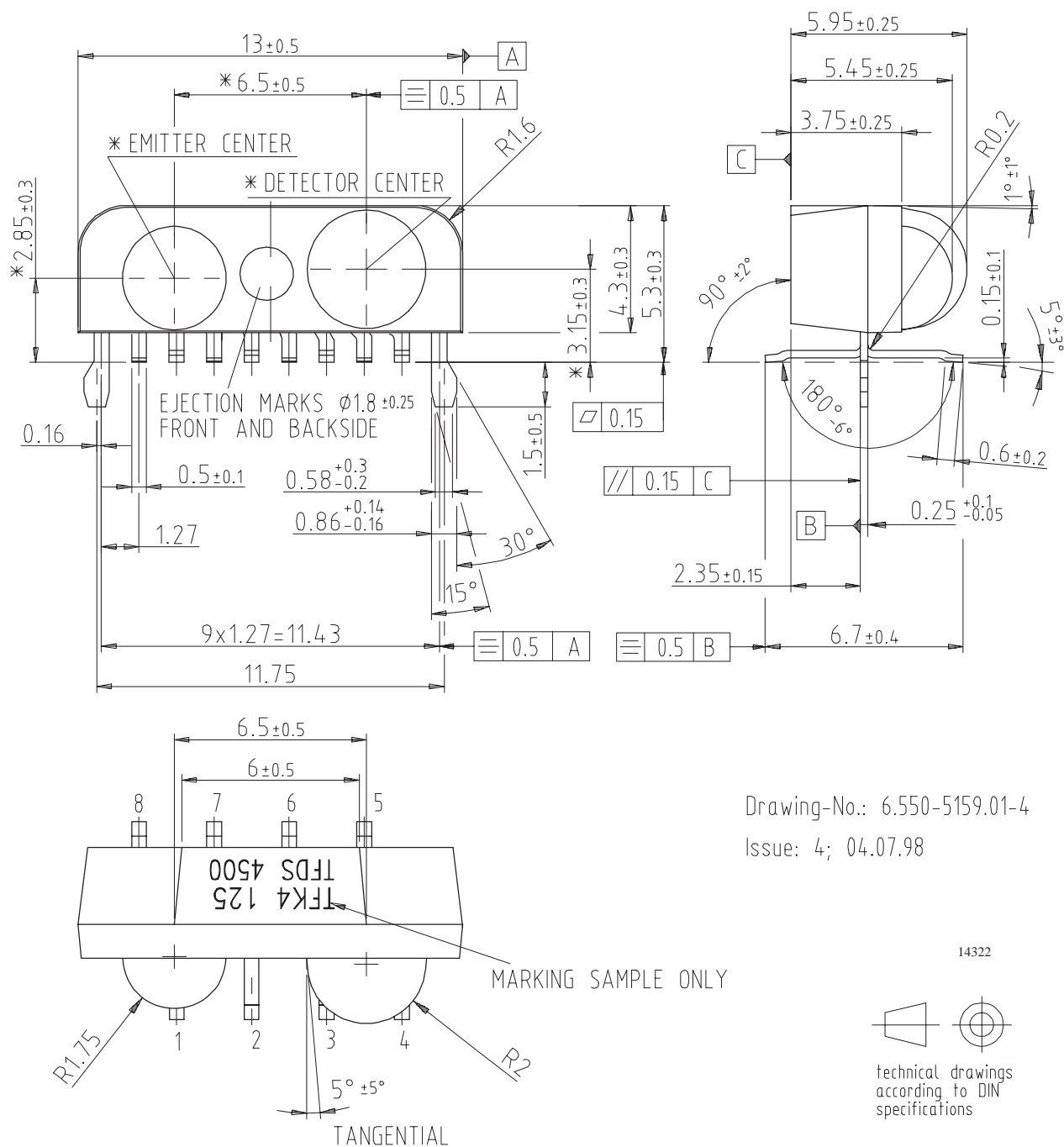


\* MARKING ORIENTATION  
180 DEGREES ALLOWED

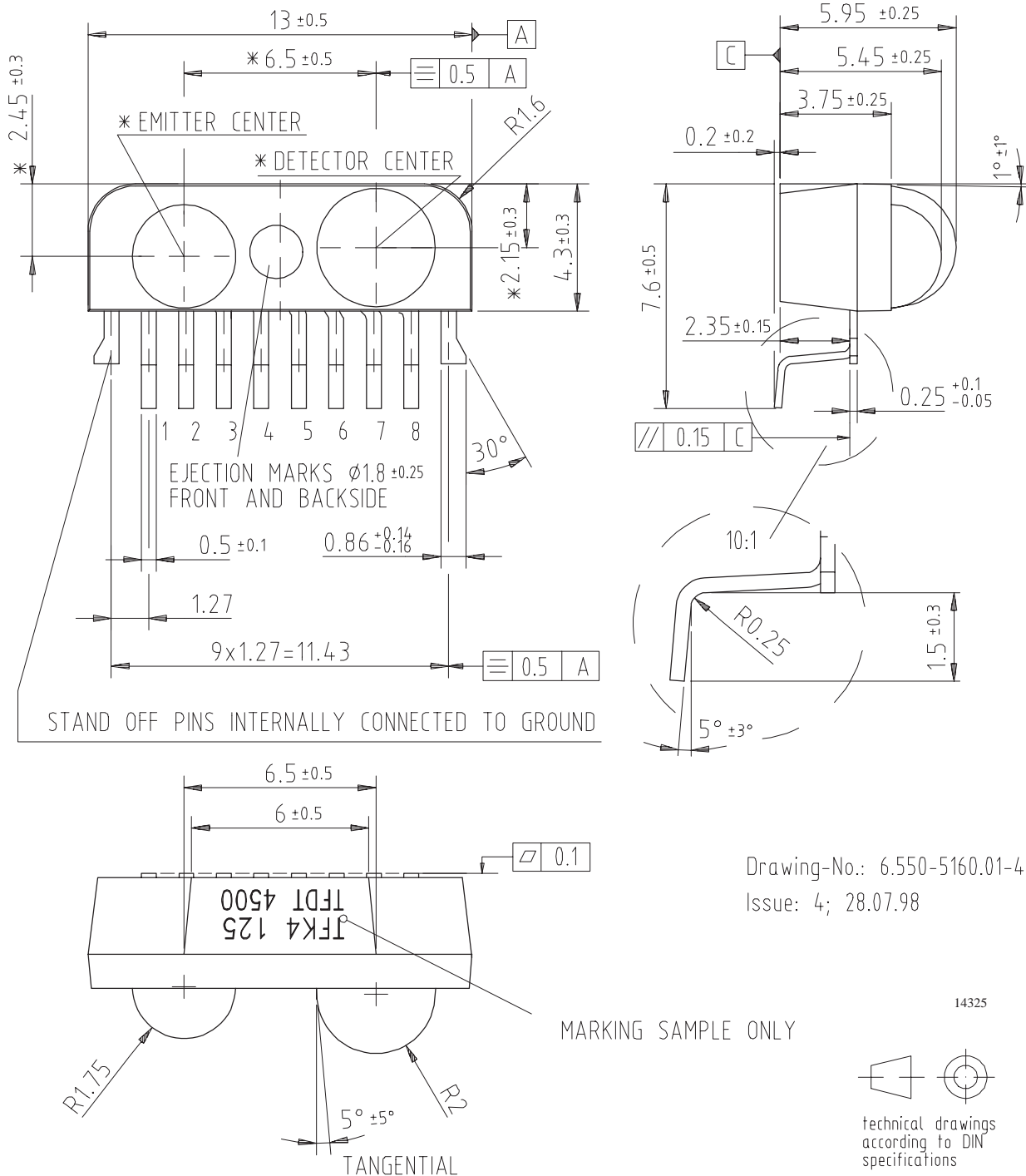
Drawing-No.: 6.550-5148.01-4  
Issue: 11; 29.01.01

12249

## TFDS4500 – Side View Package (Mechanical Dimensions)



TFDT4500 – Top View Package (Mechanical Dimensions)



Drawing-No.: 6.550-5160.01-4  
Issue: 4; 28.07.98

14325



## **Ozone Depleting Substances Policy Statement**

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany  
Telephone: 49 (0) 7131 67 2831, Fax number: 49 (0) 7131 67 2423